

MASK ROM AND THE METHOD OF FORMING THE SAME AND THE SCHEME  
OF READING THE DEVICE

ABSTRACT OF THE DISCLOSURE

The structure of the nonvolatile memory comprises a substrate having source/drain formed at unselected sides and source/drain with extension source/drain formed at other selected sides. A gate dielectric layer is formed on the substrate and a gate is formed on the gate dielectric layer. An isolation layer is formed along the surface of the gate. Spacers are formed attached on the sidewalls of the gate.